



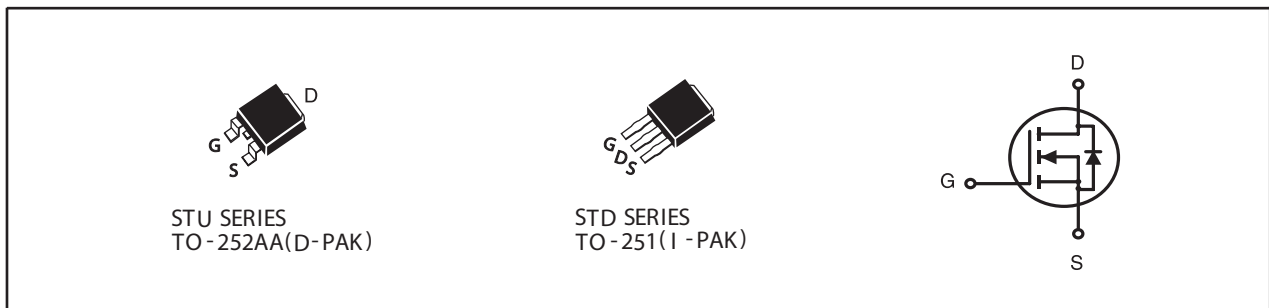
N-Channel Logic Level Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

V _{DSS}	I _D	R _{DS(ON)} (mΩ) Typ
100V	35A	21 @ V _{GS} =10V
		30 @ V _{GS} =4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- TO-252 and TO-251 Package.



ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	100	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous ^{a c}	T _C =25°C	35
		T _C =70°C	28
I _{DM}	-Pulsed ^c	102	A
E _{AS}	Single Pulse Avalanche Energy ^d	196	mJ
P _D	Maximum Power Dissipation ^a	T _C =25°C	42
		T _C =70°C	27
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θ JC}	Thermal Resistance, Junction-to-Case ^a	3	°C/W
R _{θ JA}	Thermal Resistance, Junction-to-Ambient ^a	50	°C/W

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ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	100			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =80V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V , V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	1.6	3	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =17.5A		21	26	m ohm
		V _{GS} =4.5V , I _D =15A		30	41	m ohm
g _{FS}	Forward Transconductance	V _{DS} =10V , I _D =17.5A		29		S
DYNAMIC CHARACTERISTICS ^b						
C _{ISS}	Input Capacitance	V _{DS} =25V, V _{GS} =0V f=1.0MHz		2490		pF
C _{OSS}	Output Capacitance			231		pF
C _{RSS}	Reverse Transfer Capacitance			128		pF
SWITCHING CHARACTERISTICS ^b						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =50V I _D =1A V _{GS} =10V R _{GEN} = 6 ohm		50		ns
t _r	Rise Time			43		ns
t _{D(OFF)}	Turn-Off Delay Time			75		ns
t _f	Fall Time			54		ns
Q _g	Total Gate Charge		V _{DS} =50V, I _D =17.5A, V _{GS} =10V		33	
Q _{gs}	Gate-Source Charge	V _{DS} =50V, I _D =17.5A, V _{GS} =10V		3.6		nC
Q _{gd}	Gate-Drain Charge			12		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =8A		0.78	1.3	V
Notes						
<p>a.Surface Mounted on FR4 Board of 1 inch² , 1oz.</p> <p>b.Guaranteed by design, not subject to production testing.</p> <p>c.Drain current limited by maximum junction temperature.</p> <p>d.Starting T_J=25°C, L=0.5mH, V_{DD} = 50V.(See Figure13)</p>						

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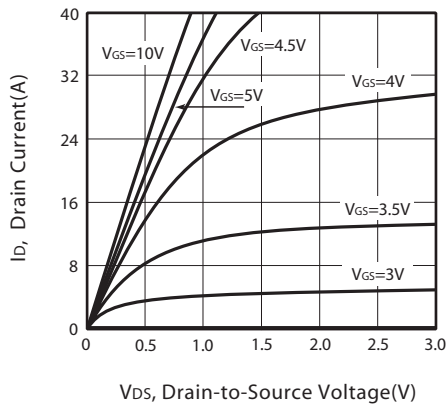


Figure 1. Output Characteristics

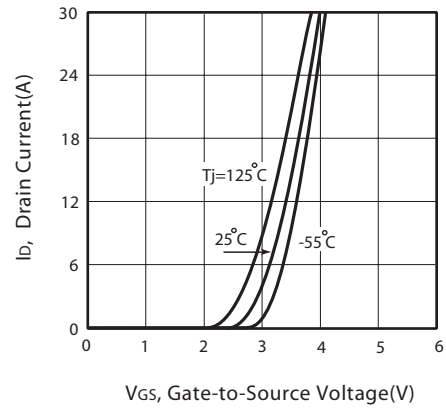


Figure 2. Transfer Characteristics

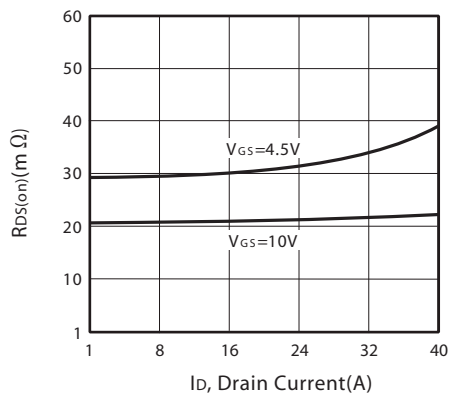


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

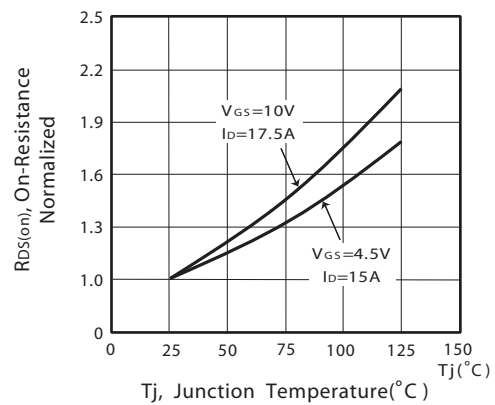


Figure 4. On-Resistance Variation with Drain Current and Temperature

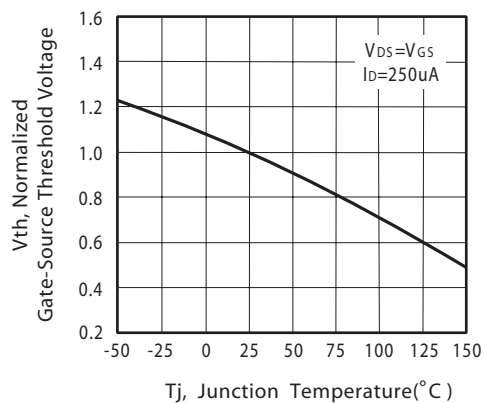


Figure 5. Gate Threshold Variation with Temperature

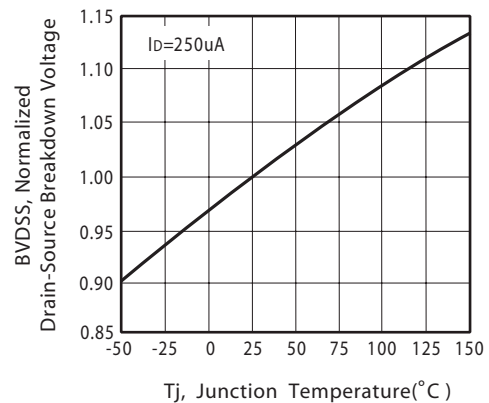


Figure 6. Breakdown Voltage Variation with Temperature

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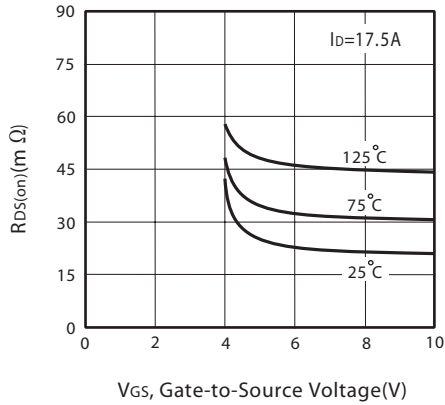


Figure 7. On-Resistance vs. Gate-Source Voltage

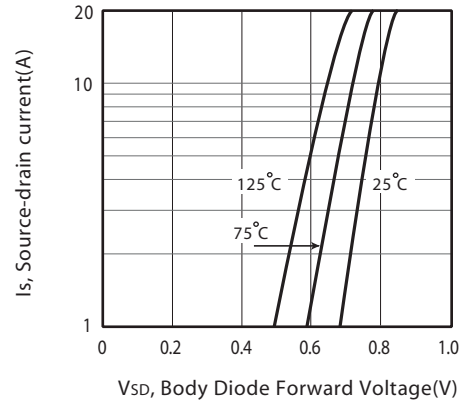


Figure 8. Body Diode Forward Voltage Variation with Source Current

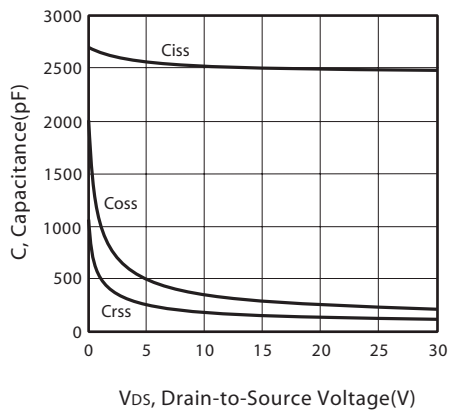


Figure 9. Capacitance

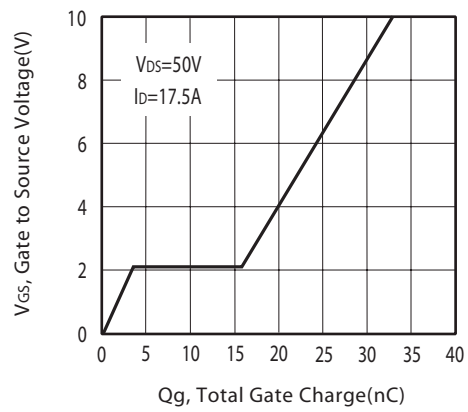


Figure 10. Gate Charge

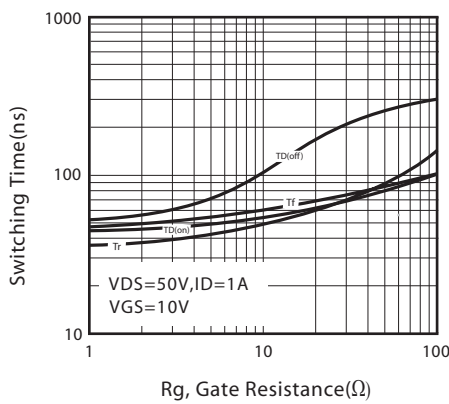


Figure 11. switching characteristics

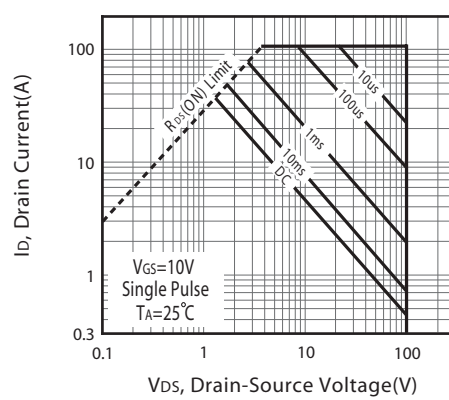
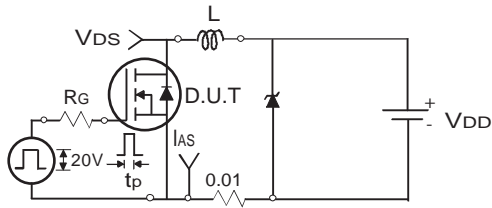


Figure 12. Maximum Safe Operating Area

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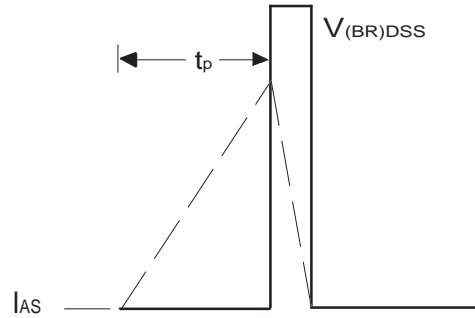
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Uncamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

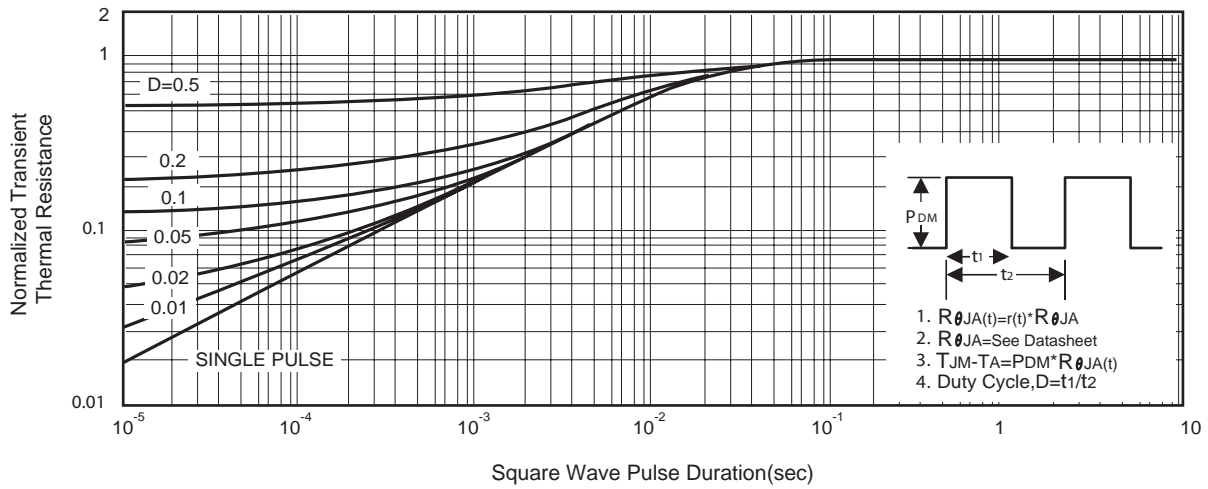


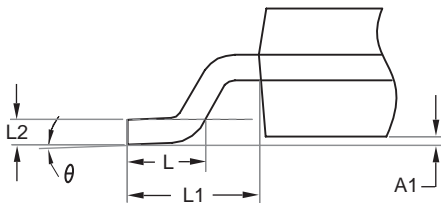
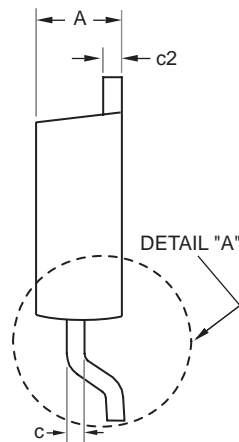
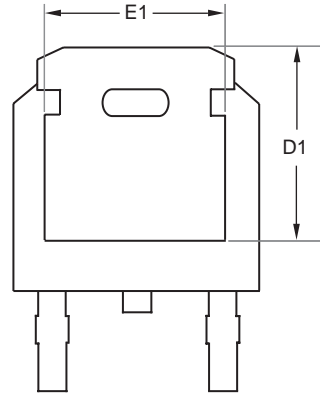
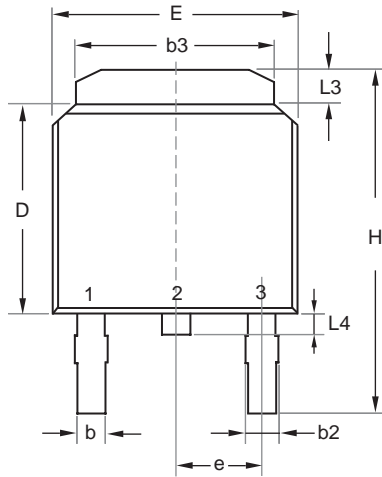
Figure 14. Normalized Thermal Transient Impedance Curve

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TO-252



DETAIL "A"

SYMBOLS	MILLIMETERS	
	MIN	MAX
A	2.200	2.380
A1	0.000	0.127
b	0.635	0.889
b2	0.762	1.143
b3	5.200	5.460
c	0.450	0.600
c2	0.450	0.580
D	6.000	6.223
D1	5.210	5.380
e	2.286 BSC	
E	6.400	6.731
E1	4.318	4.900
H	9.400	10.400
L	1.400	1.770
L1	2.743 REF	
L2	0.508 BSC	
L3	0.890	1.270
L4	0.640	1.010
θ	0°	10°

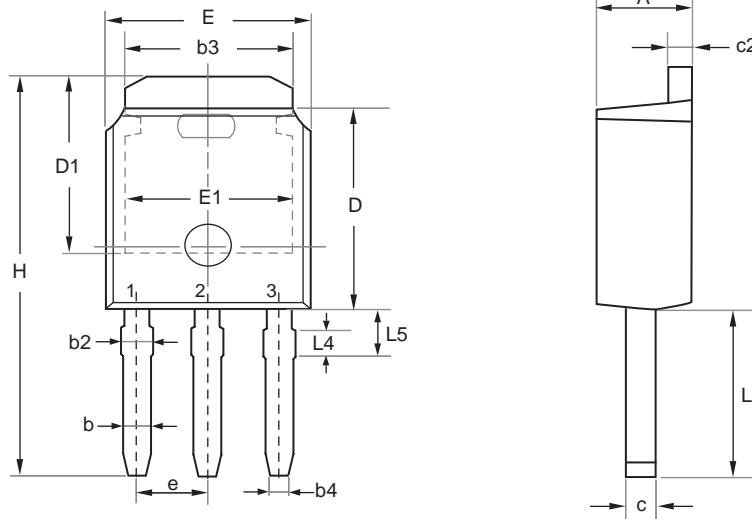
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PACKAGE OUTLINE DIMENSIONS

TO-251



SYMBOL	MILLIMETERS	
	MIN	MAX
E	6.350	6.731
L	3.700	4.400
L4	0.698 REF	
L5	0.972	1.226
D	5.970	6.223
H	9.670	11.450
b	0.630	0.850
b2	0.760	1.140
b3	4.950	5.460
b4	0.450	0.550
e	2.286 BSC	
A	2.180	2.390
c	0.400	0.610
c2	0.400	0.610
D1	5.100	---
E1	4.318	---

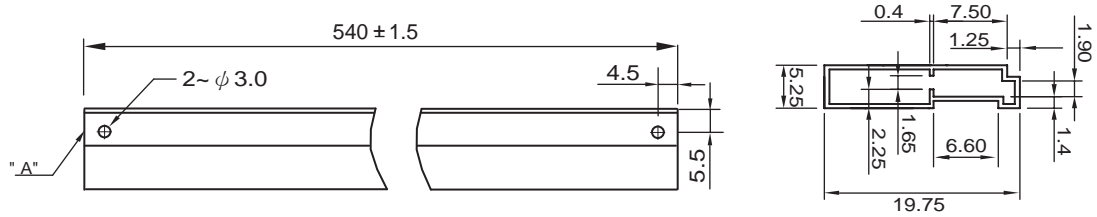
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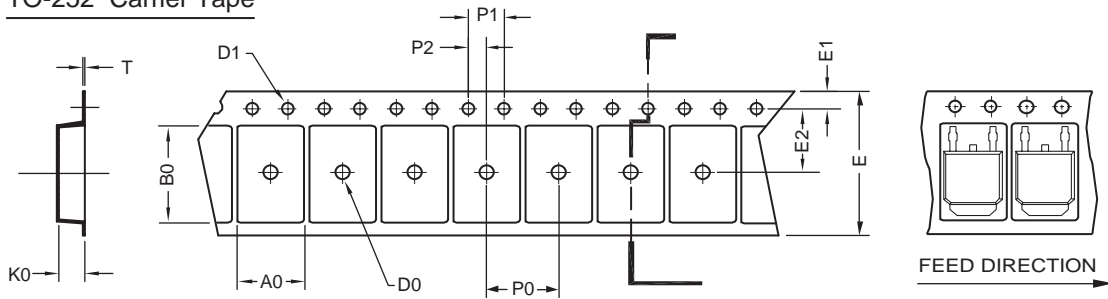
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TO-251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



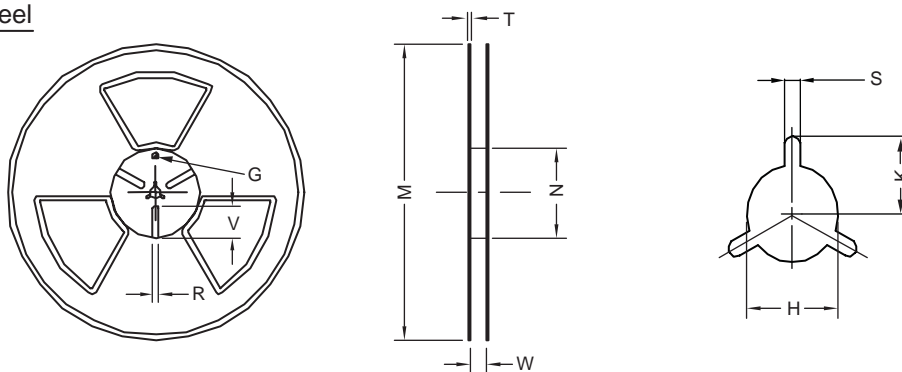
TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.96 ± 0.1	10.49 ± 0.1	2.79 ± 0.1	$\phi 2$	$\phi 1.5$ $+0.1$ -0	16.0 ± 0.3	1.75 ± 0.1	7.5 ± 0.15	8.0 ± 0.1	4.0 ± 0.1	2.0 ± 0.15	0.3 ± 0.05

TO-252 Reel



UNIT:mm

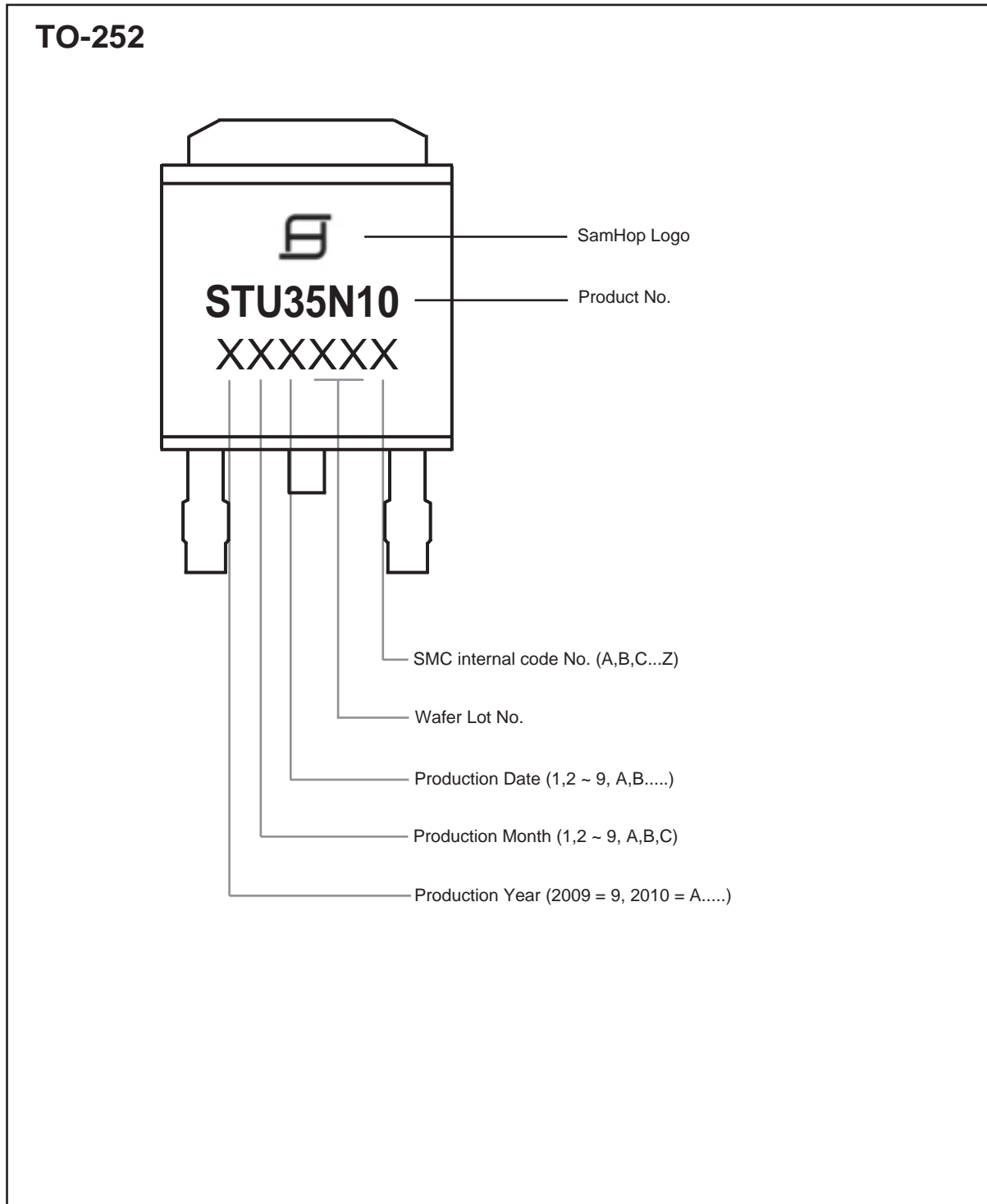
TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	$\phi 330$	$\phi 330$ ± 0.5	$\phi 97$ ± 1.0	17.0 $+1.5$ -0	2.2	$\phi 13.0$ $+0.5$ -0.2	10.6	2.0 ± 0.5	---	---	---

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TOP MARKING DEFINITION



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